Intel - EPF10K20TC144-3 Datasheet

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	144
Number of Logic Elements/Cells	1152
Total RAM Bits	12288
Number of I/O	102
Number of Gates	63000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k20tc144-3

Table 2. FLEX 10K Device Features

Feature	EPF10K70	EPF10K100 EPF10K100A	EPF10K130V	EPF10K250A
Typical gates (logic and RAM) *(1)*	70,000	100,000	130,000	250,000
Maximum system gates	118,000	158,000	211,000	310,000
LEs	3,744	4,992	6,656	12,160
LABs	468	624	832	1,520
EABs	9	12	16	20
Total RAM bits	18,432	24,576	32,768	40,960
Maximum user I/O pins	358	406	470	470

Note to tables:

(1) The embedded IEEE Std. 1149.1 JTAG circuitry adds up to 31,250 gates in addition to the listed typical or maximum system gates.

...and More Features

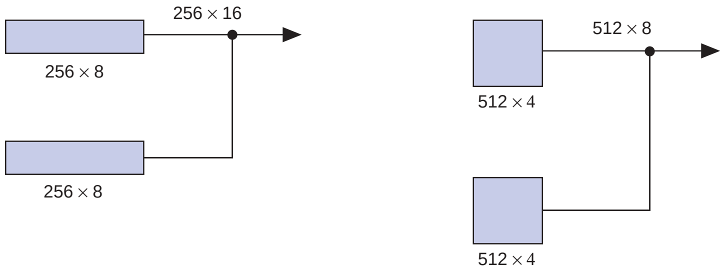
- Devices are fabricated on advanced processes and operate with a 3.3-V or 5.0-V supply voltage (see Table 3
- In-circuit reconfigurability (ICR) via external configuration device, intelligent controller, or JTAG port
- ClockLock™ and ClockBoost™ options for reduced clock delay/skew and clock multiplication
- Built-in low-skew clock distribution trees
- 100% functional testing of all devices; test vectors or scan chains are not required

Table 3. Supply Voltages for FLEX 10K & FLEX 10KA Devices

5.0-V Devices	3.3-V Devices
EPF10K10 EPF10K20 EPF10K30 EPF10K40 EPF10K50 EPF10K70 EPF10K100	EPF10K10A EPF10K30A EPF10K50V EPF10K100A EPF10K130V EPF10K250A

Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 8 RAM blocks can be combined to form a 256 × 16 RAM block; two 512 × 4 blocks of RAM can be combined to form a 512 × 8 RAM block. See Figure 3.

Figure 3. Examples of Combining EABs



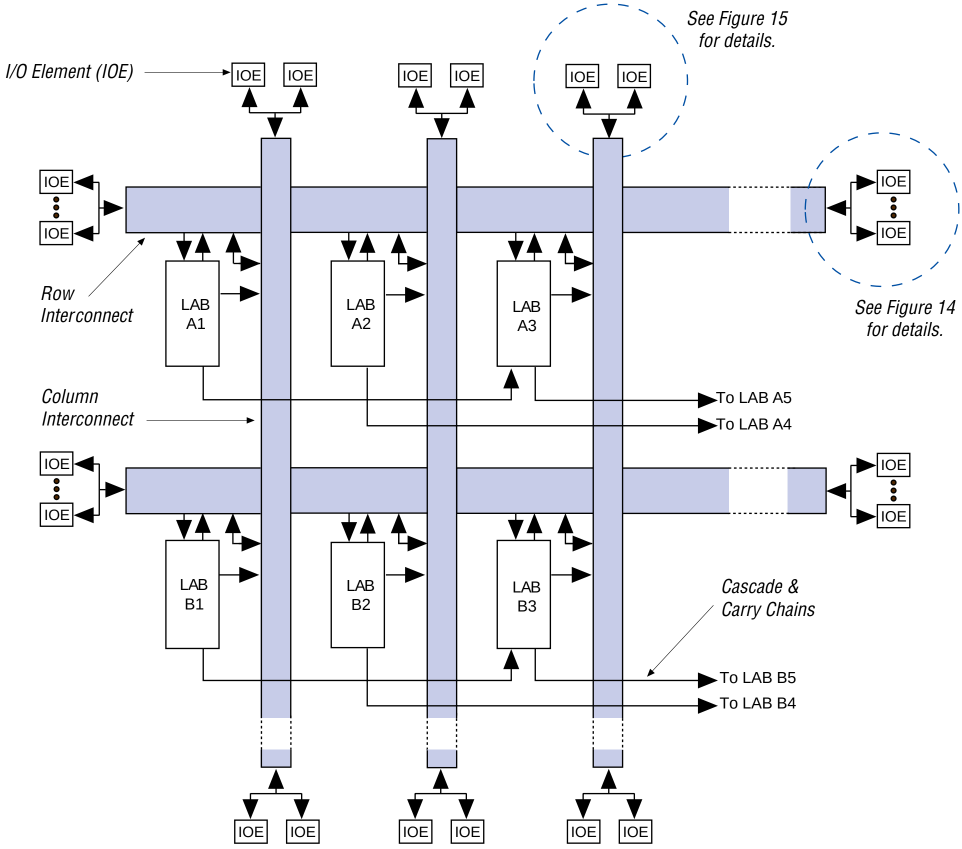
If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. Altera's software automatically combines EABs to meet a designer's RAM specifications.

EABs provide flexible options for driving and controlling clock signals. Different clocks can be used for the EAB inputs and outputs. Registers can be independently inserted on the data input, EAB output, or the address and `WE` inputs. The global signals and the EAB local interconnect can drive the `WE` signal. The global signals, dedicated clock pins, and EAB local interconnect can drive the EAB clock signals. Because the LEs drive the EAB local interconnect, the LEs can control the `WE` signal or the EAB clock signals.

Each EAB is fed by a row interconnect and can drive out to row and column interconnects. Each EAB output can drive up to two row channels and up to two column channels; the unused row channel can be driven by other LEs. This feature increases the routing resources available for EAB outputs. See Figure 4.

Figure 12 shows the interconnection of adjacent LABs and EABs with row, column, and local interconnects, as well as the associated cascade and carry chains. Each LAB is labeled according to its location: a letter represents the row and a number represents the column. For example, LAB B3 is in row B, column 3.

Figure 12. Interconnect Resources



Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across devices; it provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, an LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal will reset all IOE registers, overriding any other control signals.

Tables 8 and 9 list the sources for each peripheral control signal, and the rows that can drive global signals. These tables also show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals.

Table 8. EPF10K10, EPF10K20, EPF10K30, EPF10K40 & EPF10K50 Peripheral Bus Sources

Peripheral Control Signal	EPF10K10 EPF10K10A	EPF10K20	EPF10K30 EPF10K30A	EPF10K40	EPF10K50 EPF10K50V
`OE0`	Row A	Row A	Row A	Row A	Row A
`OE1`	Row A	Row B	Row B	Row C	Row B
`OE2`	Row B	Row C	Row C	Row D	Row D
`OE3`	Row B	Row D	Row D	Row E	Row F
`OE4`	Row C	Row E	Row E	Row F	Row H
`OE5`	Row C	Row F	Row F	Row G	Row J
`CLKENA0/CLK0/GLOBAL0`	Row A	Row A	Row A	Row B	Row A
`CLKENA1/OE6/GLOBAL1`	Row A	Row B	Row B	Row C	Row C
`CLKENA2/CLR0`	Row B	Row C	Row C	Row D	Row E
`CLKENA3/OE7/GLOBAL2`	Row B	Row D	Row D	Row E	Row G
`CLKENA4/CLR1`	Row C	Row E	Row E	Row F	Row I
`CLKENA5/CLK1/GLOBAL3`	Row C	Row F	Row F	Row H	Row J

Table 9. EPF10K70, EPF10K100, EPF10K130V & EPF10K250A Peripheral Bus Sources

Peripheral Control Signal	EPF10K70	EPF10K100 EPF10K100A	EPF10K130V	EPF10K250A
`OE0`	Row A	Row A	Row C	Row E
`OE1`	Row B	Row C	Row E	Row G
`OE2`	Row D	Row E	Row G	Row I
`OE3`	Row I	Row L	Row N	Row P
`OE4`	Row G	Row I	Row K	Row M
`OE5`	Row H	Row K	Row M	Row O
`CLKENA0/CLK0/GLOBAL0`	Row E	Row F	Row H	Row J
`CLKENA1/OE6/GLOBAL1`	Row C	Row D	Row F	Row H
`CLKENA2/CLR0`	Row B	Row B	Row D	Row F
`CLKENA3/OE7/GLOBAL2`	Row F	Row H	Row J	Row L
`CLKENA4/CLR1`	Row H	Row J	Row L	Row N
`CLKENA5/CLK1/GLOBAL3`	Row E	Row G	Row I	Row K

Figure 15. FLEX 10K Column-to-IOE Connections

The values for m and n are provided in Table 11.

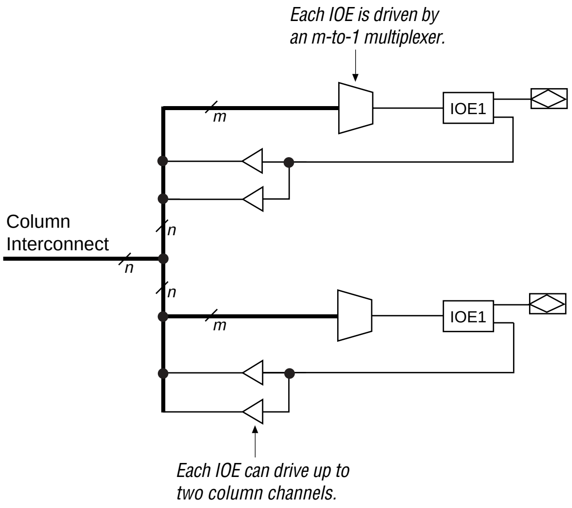


Table 11 lists the FLEX 10K column-to-IOE interconnect resources.

Table 11. FLEX 10K Column-to-IOE Interconnect Resources

Device	Channels per Column (*n*)	Column Channel per Pin (*m*)
EPF10K10 EPF10K10A	24	16
EPF10K20	24	16
EPF10K30 EPF10K30A	24	16
EPF10K40	24	16
EPF10K50 EPF10K50V	24	16
EPF10K70	24	16
EPF10K100 EPF10K100A	24	16
EPF10K130V	32	24
EPF10K250A	40	32

Table 24. EPF10K50V & EPF10K130V Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		2.0		5.75	V
V_{IL}	Low-level input voltage		–0.5		0.8	V
V_{OH}	3.3-V high-level TTL output voltage	I_{OH} = –8 mA DC *(8)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC *(8)*	V_{CCIO} – 0.2			V
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 8 mA DC *(9)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC *(9)*			0.2	V
I_I	Input pin leakage current	V_I = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.3	10	mA
		V_I = ground, no load *(11)*		10		mA

Table 25. EPF10K50V & EPF10K130V Device Capacitance *(12)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		15	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

Notes to tables:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.

(2) Minimum DC input voltage is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.

(3) Numbers in parentheses are for industrial-temperature-range devices.

(4) Maximum V_{CC} rise time is 100 ms. V_{CC} must rise monotonically.

(5) EPF10K50V and EPF10K130V device inputs may be driven before V_{CCINT} and V_{CCIO} are powered.

(6) Typical values are for T_A = 25° C and V_{CC} = 3.3 V.

(7) These values are specified under the EPF10K50V and EPF10K130V device Recommended Operating Conditions in Table 23 on page 48.

(8) The I_{OH} parameter refers to high-level TTL or CMOS output current.

(9) The I_{OL} parameter refers to low-level TTL or CMOS output current. This parameter applies to open-drain pins as well as output pins.

(10) This value is specified for normal device operation. The value may vary during power-up.

(11) This parameter applies to -1 speed grade EPF10K50V devices, -2 speed grade EPF10K50V industrial temperature devices, and -2 speed grade EPF10K130V devices.

(12) Capacitance is sample-tested only.

Timing simulation and delay prediction are available with the MAX+PLUS II Simulator and Timing Analyzer, or with industry-standard EDA tools. The Simulator offers both pre-synthesis functional simulation to evaluate logic design accuracy and post-synthesis timing simulation with 0.1-ns resolution. The Timing Analyzer provides point-to-point timing delay information, setup and hold time analysis, and device-wide performance analysis.

Figure 24 shows the overall timing model, which maps the possible paths to and from the various elements of the FLEX 10K device.

Figure 24. FLEX 10K Device Timing Model

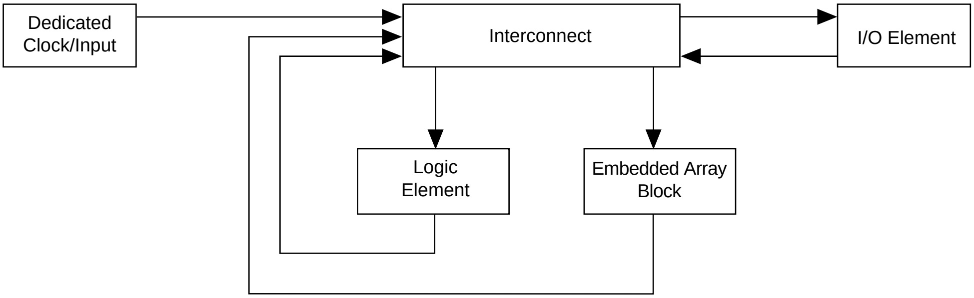


Table 34. EAB Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{EABDATA1}$	Data or address delay to EAB for combinatorial input	
$t_{EABDATA2}$	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
$t_{EABBYPASS}$	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{AA}	Address access delay	
t_{WP}	Write pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	*(5)*
t_{WDH}	Data hold time after falling edge of write pulse	*(5)*
t_{WASU}	Address setup time before rising edge of write pulse	*(5)*
t_{WAH}	Address hold time after falling edge of write pulse	*(5)*
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

Table 45. EPF10K10 & EPF10K20 Device External Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{DRR}		16.1		20.0	ns
t_{INSU} (2), (3)	5.5		6.0		ns
t_{INH} (3)	0.0		0.0		ns
t_{OUTCO} (3)	2.0	6.7	2.0	8.4	ns

Table 46. EPF10K10 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.5		5.6		ns
$t_{INHBIDIR}$	0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	6.7	2.0	8.4	ns
$t_{XZBIDIR}$		10.5		13.4	ns
$t_{ZXBIDIR}$		10.5		13.4	ns

Table 47. EPF10K20 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.6		5.7		ns
$t_{INHBIDIR}$	0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	6.7	2.0	8.4	ns
$t_{XZBIDIR}$		10.5		13.4	ns
$t_{ZXBIDIR}$		10.5		13.4	ns

Notes to tables:

(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Table 68. EPF10K100 Device Interconnect Timing Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		10.3		10.3		12.2	ns
t_{DIN2LE}		4.8		4.8		6.0	ns
$t_{DIN2DATA}$		7.3		7.3		11.0	ns
$t_{DCLK2IOE}$ without ClockLock or ClockBoost circuitry		6.2		6.2		7.7	ns
$t_{DCLK2IOE}$ with ClockLock or ClockBoost circuitry		2.3		–		–	ns
$t_{DCLK2LE}$ without ClockLock or ClockBoost circuitry		4.8		4.8		6.0	ns
$t_{DCLK2LE}$ with ClockLock or ClockBoost circuitry		2.3		–		–	ns
$t_{SAMELAB}$		0.4		0.4		0.5	ns
$t_{SAMEROW}$		4.9		4.9		5.5	ns
$t_{SAMECOLUMN}$		5.1		5.1		5.4	ns
$t_{DIFFROW}$		10.0		10.0		10.9	ns
$t_{TWOROWS}$		14.9		14.9		16.4	ns
$t_{LEPERIPH}$		6.9		6.9		8.1	ns
$t_{LABCARRY}$		0.9		0.9		1.1	ns
$t_{LABCASC}$		3.0		3.0		3.2	ns

Table 73. EPF10K50V Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.7		2.8		3.4		4.6	ns
$t_{EABDATA2}$		4.9		3.9		4.8		5.9	ns
t_{EABWE1}		0.0		2.5		3.0		3.7	ns
t_{EABWE2}		4.0		4.1		5.0		6.2	ns
t_{EABCLK}		0.4		0.8		1.0		1.2	ns
t_{EABCO}		0.1		0.2		0.3		0.4	ns
$t_{EABBYPASS}$		0.9		1.1		1.3		1.6	ns
t_{EABSU}	0.8		1.5		1.8		2.2		ns
t_{EABH}	0.8		1.6		2.0		2.5		ns
t_{AA}		5.5		8.2		10.0		12.4	ns
t_{WP}	6.0		4.9		6.0		7.4		ns
t_{WDSU}	0.1		0.8		1.0		1.2		ns
t_{WDH}	0.1		0.2		0.3		0.4		ns
t_{WASU}	0.1		0.4		0.5		0.6		ns
t_{WAH}	0.1		0.8		1.0		1.2		ns
t_{WO}		2.8		4.3		5.3		6.5	ns
t_{DD}		2.8		4.3		5.3		6.5	ns
t_{EABOUT}		0.5		0.4		0.5		0.6	ns
t_{EABCH}	2.0		4.0		4.0		4.0		ns
t_{EABCL}	6.0		4.9		6.0		7.4		ns

Table 75. EPF10K50V Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.7		6.0		7.1		8.2	ns
t_{DIN2LE}		2.5		2.6		3.1		3.9	ns
$t_{DIN2DATA}$		4.4		5.9		6.8		7.7	ns
$t_{DCLK2IOE}$		2.5		3.9		4.7		5.5	ns
$t_{DCLK2LE}$		2.5		2.6		3.1		3.9	ns
$t_{SAMELAB}$		0.2		0.2		0.3		0.3	ns
$t_{SAMEROW}$		2.8		3.0		3.2		3.4	ns
$t_{SAMECOLUMN}$		3.0		3.2		3.4		3.6	ns
$t_{DIFFROW}$		5.8		6.2		6.6		7.0	ns
$t_{TWOROWS}$		8.6		9.2		9.8		10.4	ns
$t_{LEPERIPH}$		4.5		5.5		6.1		7.0	ns
$t_{LABCARRY}$		0.3		0.4		0.5		0.7	ns
$t_{LABCASC}$		0.0		1.3		1.6		2.0	ns

Table 76. EPF10K50V Device External Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{DRR}		11.2		14.0		17.2		21.1	ns
t_{INSU} *(2), (3)*	5.5		4.2		5.2		6.9		ns
t_{INH} *(3)*	0.0		0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.9	2.0	7.8	2.0	9.5	2.0	11.1	ns

Table 77. EPF10K50V Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.0		2.8		3.5		4.1		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.9	2.0	7.8	2.0	9.5	2.0	11.1	ns
$t_{XZBIDIR}$		8.0		9.8		11.8		14.3	ns
$t_{ZXBIDIR}$		8.0		9.8		11.8		14.3	ns

Notes to tables:

(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 78 through 84 show EPF10K130V device internal and external timing parameters.

Table 78. EPF10K130V Device LE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.3		1.8		2.3	ns
t_{CLUT}		0.5		0.7		0.9	ns
t_{RLUT}		1.2		1.7		2.2	ns
t_{PACKED}		0.5		0.6		0.7	ns
t_{EN}		0.6		0.8		1.0	ns
t_{CICO}		0.2		0.3		0.4	ns
t_{CGEN}		0.3		0.4		0.5	ns
t_{CGENR}		0.7		1.0		1.3	ns
t_{CASC}		0.9		1.2		1.5	ns
t_{C}		1.9		2.4		3.0	ns
t_{CO}		0.6		0.9		1.1	ns
t_{COMB}		0.5		0.7		0.9	ns
t_{SU}	0.2		0.2		0.3		ns
t_{H}	0.0		0.0		0.0		ns
t_{PRE}		2.4		3.1		3.9	ns
t_{CLR}		2.4		3.1		3.9	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 87. EPF10K10A Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		3.3		3.9		5.2	ns
$t_{EABDATA2}$		1.0		1.3		1.7	ns
t_{EABWE1}		2.6		3.1		4.1	ns
t_{EABWE2}		2.7		3.2		4.3	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		1.2		1.4		1.8	ns
$t_{EABBYPASS}$		0.1		0.2		0.2	ns
t_{EABSU}	1.4		1.7		2.2		ns
t_{EABH}	0.1		0.1		0.1		ns
t_{AA}		4.5		5.4		7.3	ns
t_{WP}	2.0		2.4		3.2		ns
t_{WDSU}	0.7		0.8		1.1		ns
t_{WDH}	0.5		0.6		0.7		ns
t_{WASU}	0.6		0.7		0.9		ns
t_{WAH}	0.9		1.1		1.5		ns
t_{WO}		3.3		3.9		5.2	ns
t_{DD}		3.3		3.9		5.2	ns
t_{EABOUT}		0.1		0.1		0.2	ns
t_{EABCH}	3.0		3.5		4.0		ns
t_{EABCL}	3.03		3.5		4.0		ns

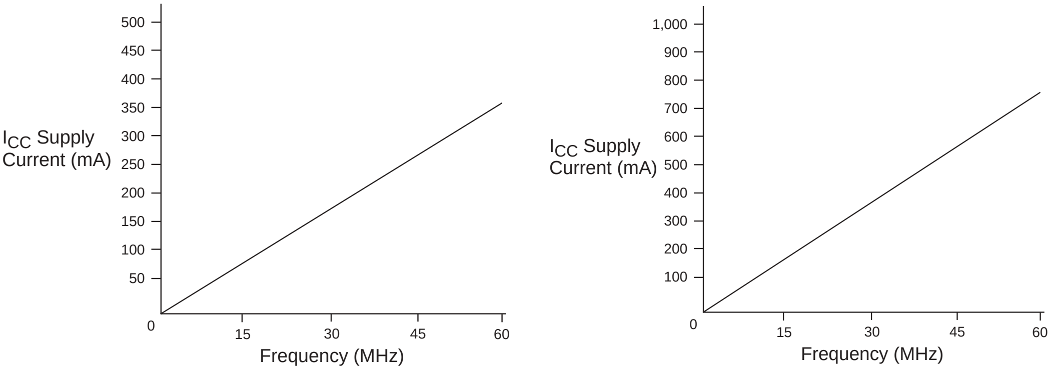
Table 93. EPF10K30A Device IOE Timing Microparameters *Note (1)* **(Part 2 of 2)**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOH}	0.9		1.1		1.4		ns
t_{IOCLR}		0.7		0.8		1.0	ns
t_{OD1}		1.9		2.2		2.9	ns
t_{OD2}		4.8		5.6		7.3	ns
t_{OD3}		7.0		8.2		10.8	ns
t_{XZ}		2.2		2.6		3.4	ns
t_{ZX1}		2.2		2.6		3.4	ns
t_{ZX2}		5.1		6.0		7.8	ns
t_{ZX3}		7.3		8.6		11.3	ns
t_{INREG}		4.4		5.2		6.8	ns
t_{IOFD}		3.8		4.5		5.9	ns
t_{INCOMB}		3.8		4.5		5.9	ns

Table 95. EPF10K30A Device EAB Internal Timing Macroparameters *Note (1)*

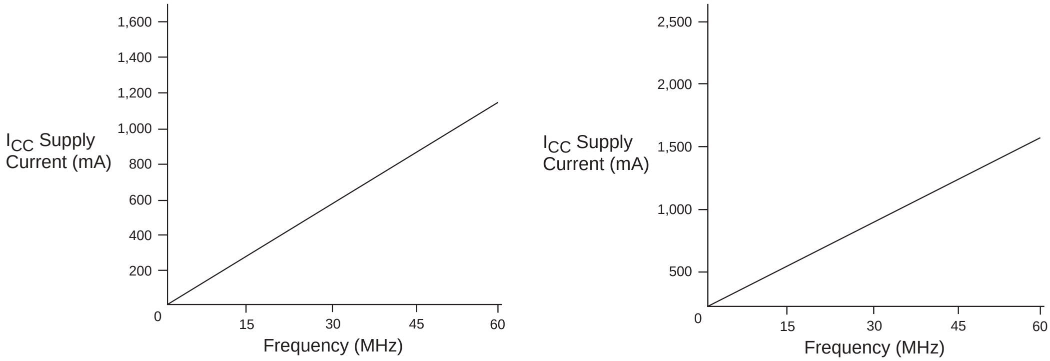
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		9.7		11.6		16.2	ns
$t_{EABRCCOMB}$	9.7		11.6		16.2		ns
$t_{EABRCREG}$	5.9		7.1		9.7		ns
t_{EABWP}	3.8		4.5		5.9		ns
$t_{EABWCCOMB}$	4.0		4.7		6.3		ns
$t_{EABWCREG}$	9.8		11.6		16.6		ns
t_{EABDD}		9.2		11.0		16.1	ns
$t_{EABDATACO}$		1.7		2.1		3.4	ns
$t_{EABDATASU}$	2.3		2.7		3.5		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	3.3		3.9		4.9		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	3.2		3.8		5.0		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.7		4.4		5.1		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		6.1		7.3		11.3	ns

Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 1 of 3)



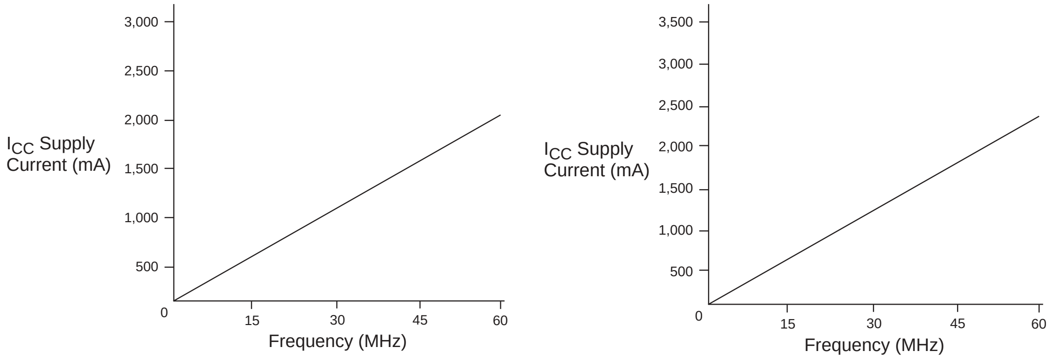
EPF10K10

EPF10K20



EPF10K30

EPF10K40

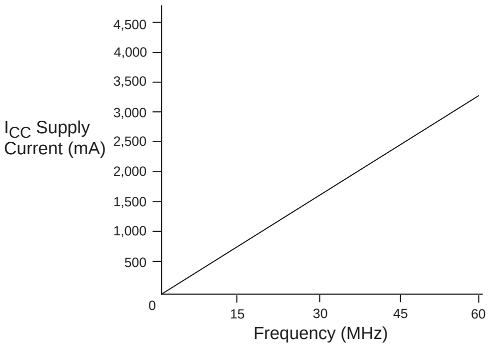


EPF10K50

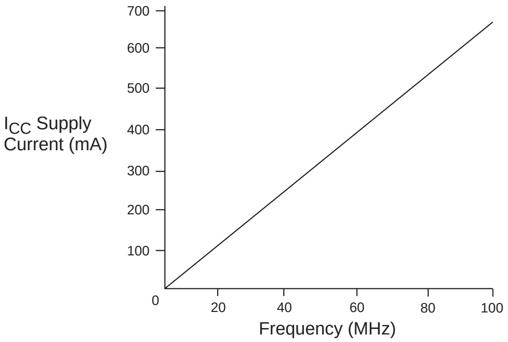
EPF10K70

Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 2 of 3)

EPF10K100



EPF10K50V



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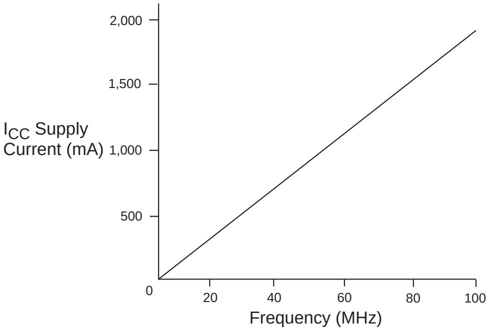

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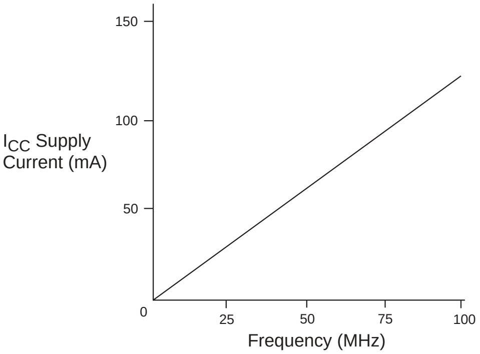

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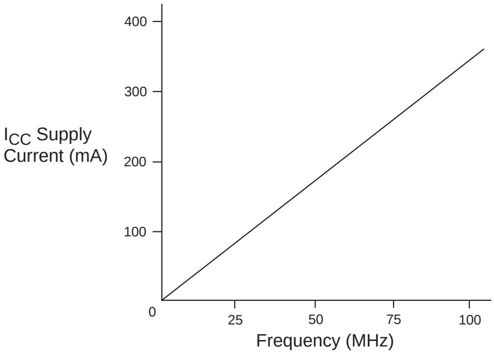

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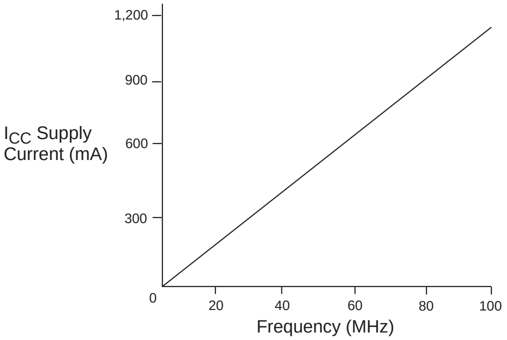

Multiple FLEX 10K devices can be configured in any of the five configuration schemes by connecting the configuration enable (`nCE`) and configuration enable output (`nCEO`) pins on each device.

Table 116. Data Sources for Configuration

Configuration Scheme	Data Source
Configuration device	EPC1, EPC2, EPC16, or EPC1441 configuration device
Passive serial (PS)	BitBlaster, MasterBlaster, or ByteBlasterMV download cable, or serial data source
Passive parallel asynchronous (PPA)	Parallel data source
Passive parallel synchronous (PPS)	Parallel data source
JTAG	BitBlaster, MasterBlaster, or ByteBlasterMV download cable, or microprocessor with Jam STAPL file or Jam Byte-Code file

Device Pin-Outs

See the Altera web site (**http://www.altera.com**) or the Altera Digital Library for pin-out information.

Revision History

The information contained in the *FLEX 10K Embedded Programmable Logic Device Family Data Sheet* version 4.2 supersedes information published in previous versions.

Version 4.2 Changes

The following change was made to version 4.2 of the *FLEX 10K Embedded Programmable Logic Device Family Data Sheet*: updated Figure 13.

Version 4.1 Changes

The following changes were made to version 4.1 of the *FLEX 10K Embedded Programmable Logic Device Family Data Sheet*.

- Updated General Description section
- Updated I/O Element section
- Updated SameFrame Pin-Outs section
- Updated Figure 16
- Updated Tables 13 and 116
- Added Note 9 to Table 19
- Added Note 10 to Table 24
- Added Note 10 to Table 28